speed; correcting the film thickness of the substrate obtained during polishing of the substrate in the time intervals using the amount of change as a correction value; and identifying the maximum film thickness value and the minimum film thickness value based on the corrected film thickness of the substrate.

[0025] In an embodiment, determining in advance by a recipe setting whether to control the pressure of the pressure chamber associated with the maximum film thickness value so that the average thickness value of the substrate corresponding to the pressure chamber associated with the maximum thickness value is less than the average thickness value of the entire substrate when the pressure chamber associated with the maximum film thickness value and the pressure chamber associated with the minimum film thickness value are the same pressure chamber, or to control the pressure of the pressure chamber associated with the minimum film thickness value so that the average thickness value of the substrate corresponding to the pressure chamber associated with the minimum film thickness value is higher than the average thickness value of the entire substrate.

In an embodiment, comparing a first difference between the maximum film thickness value and the average film thickness value of the entire substrate and a second difference between the minimum film thickness value and the average film thickness value of the entire substrate when the pressure chamber associated with the maximum film thickness value and the pressure chamber associated with the minimum film thickness value are the same pressure chamber; controlling the pressure of the pressure chamber associated with the maximum film thickness value so that the average film thickness value of the substrate corresponding to the pressure chamber associated with the maximum film thickness value is lower than the average film thickness value of the entire substrate when the first difference is higher than the second difference; and controlling the pressure of the pressure chamber associated with the minimum film thickness value so that the average film thickness value of the substrate corresponding to the pressure chamber associated with the minimum film thickness value is higher than the average film thickness value of the entire substrate when the second difference is higher